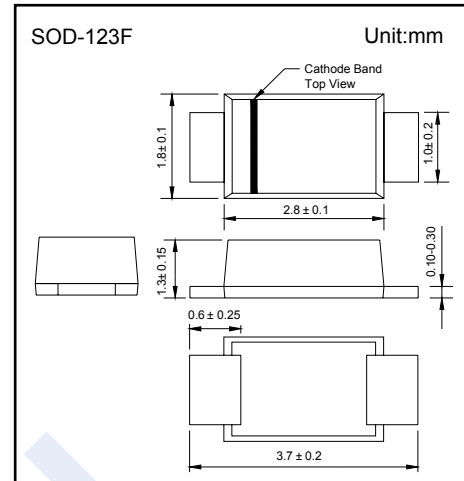


Schottky Diodes

MBRS230F

■ Features

- High forward surge current capability
- For surface mounted applications
- Metal silicon junction, majority carrier conduction
- Low reverse leakage
- High temperature soldering guaranteed:
250°C/10 seconds at terminals



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Peak Repetitive Reverse Voltage	VRRM	30	V
DC Blocking Voltage	VDC	30	
RMS Reverse Voltage	V _{R(RMS)}	21	
Forward Voltage @ I _F = 2A	V _{FM}	0.55	
Average Rectified Output Current @ T _L = 75°C	I _{FAV}	2	A
Non-Repetitive Peak Forward Surge Current @ 8.3ms	I _{FSM}	30	
Reverse voltage leakage current	I _R	@ T _a = 25°C	mA
		@ T _a = 100°C	
Junction capacitance	C _j	220	pF
Thermal Resistance Junction to Ambient	R _{θJA}	75	°C/W
Junction Temperature	T _J	125	°C
Storage Temperature range	T _{stg}	-65 to 150	

■ Marking

Marking	L3N
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Typical Characteristics

